(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
19 January 2006 (19.01.2006)

PCT

(10) International Publication Number
WO 2006/007462 A1

(51) International Patent Classification[7]: H01L 21/765, 21/8242

(21) International Application Number: PCT/US2005/021787

(22) International Filing Date: 21 June 2005 (21.06.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/873,226 23 June 2004 (23.06.2004) US

(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; 8000 S. Federal Way, Boise, ID 83707-0006 (US).

(72) Inventor; and

(75) Inventor/Applicant *(for US only)*: **MOULI, Chandra** [US/US]; 727 South Granite Way, Boise, ID 83712 (US).

(74) Agent: **D'AMICO, Thomas, J.**; Dickstein Shapiro Morin & Oshinsky LLP, 2101 L Street NW, Washington, DC 20037-1526 (US).

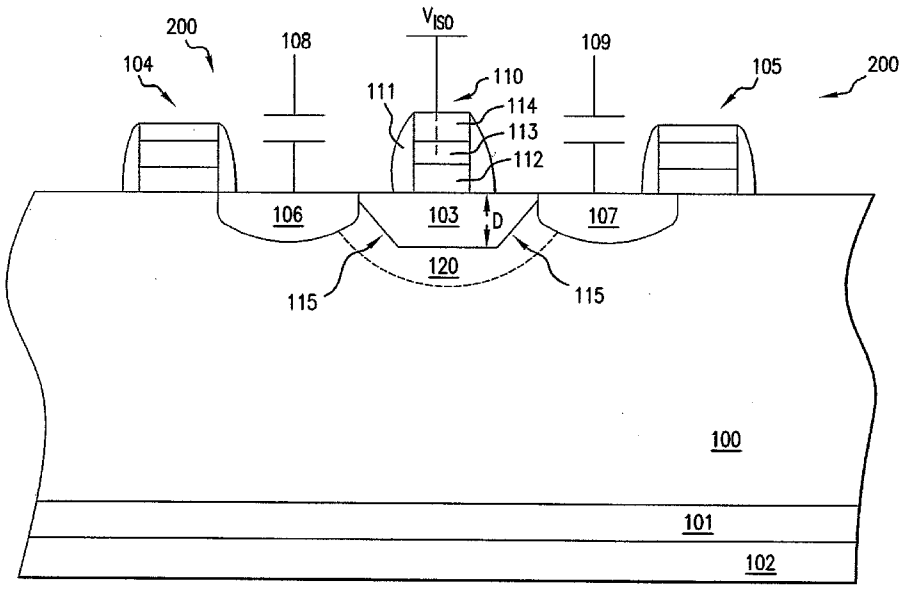
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) **Title:** ISOLATION STRUCTURE FOR A MEMORY CELL USING Al_2O_3 DIELECTRIC



(57) **Abstract:** The invention provides, in one exemplary embodiment, an isolation gate formed over a substrate for biasing the substrate and providing isolation between adjacent active areas of an integrated circuit structure, for example a DRAM memory cell. An aluminum oxide (Al_2O_3) is used as a gate dielectric, rather than a conventional gate oxide layer, to create a hole-rich accumulation region under and near the trench isolation region. Another exemplary embodiment of the invention provides an aluminum oxide layer utilized as a liner in a shallow trench isolation (STI) region to increase the effectiveness of the isolation region. The embodiments may also be used together at an isolation region.

WO 2006/007462 A1